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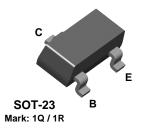
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2N5088 2N5089

## MMBT5088 MMBT5089





## **NPN General Purpose Amplifier**

This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from  $1\mu A$  to 50 mA.

## Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter		Value	Units
$V_{CEO}$	Collector-Emitter Voltage	2N5088	30	V
		2N5089	25	V
$V_{CBO}$	Collector-Base Voltage	2N5088	35	V
		2N5089	30	V
V <sub>EBO</sub>	Emitter-Base Voltage		4.5	V
I <sub>C</sub>	Collector Current - Continuous		100	mA
T <sub>J</sub> , T <sub>sta</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5088 2N5089	*MMBT5088 *MMBT5089	
P <sub>D</sub>	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

(continued)

8.0

#### **Electrical Characteristics**

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min	Max	Units
OFF CHAF	RACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0	5088 5089	30 25		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \ \mu A, \ I_E = 0$	5088 5089	35 30		V V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0 V <sub>CB</sub> = 15 V, I <sub>E</sub> = 0	5088 5089		50 50	nA nA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 3.0 V, I <sub>C</sub> = 0 V <sub>EB</sub> = 4.5 V, I <sub>C</sub> = 0			50 100	nA nA
	ACTERISTICS			1		
h <sub>FE</sub>	DC Current Gain	$I_C = 100 \mu A, V_{CE} = 5.0 V$ $I_C = 1.0 mA, V_{CE} = 5.0 V$	5088 5089 5088	300 400 350 450	900 1200	
		$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}^*$	5089 5088 5089	300 400		
VCE(sat)	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	-		0.5	V

### SMALL SIGNAL CHARACTERISTICS

Base-Emitter On Voltage

f <sub>T</sub>	Current Gain - Bandwidth Product	$I_C = 500 \mu\text{A}, V_{CE} = 5.0 \text{mA},$ f = 20 MHz	50		MHz
Ccb	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0, f = 100 \text{ kHz}$		4.0	pF
C <sub>eb</sub>	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0, f = 100 \text{ kHz}$		10	pF
h <sub>fe</sub>	Small-Signal Current Gain	I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 5.0 V, <b>5088</b> f = 1.0 kHz <b>5089</b>	350 450	1400 1800	
NF	Noise Figure	$I_{C} = 100 \ \mu A, \ V_{CE} = 5.0 \ V, \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $		3.0 2.0	dB dB

 $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ 

## **Spice Model**

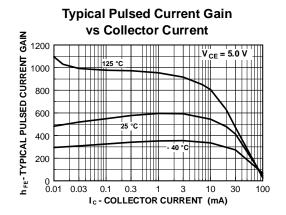
 $V_{BE(on)}$ 

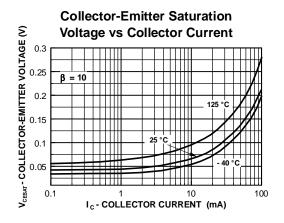
 $NPN \ (Is=5.911f \ Xti=3 \ Eg=1.11 \ Vaf=62.37 \ Bf=1.122K \ Ne=1.394 \ Is==5.911f \ Ikf=14.92m \ Xtb=1.5 \ Br=1.271 \ Nc=2 \ Isc=0 \ Ikr=0 \ Rc=1.61 \ Cjc=4.017p \ Mjc=.3174 \ Vjc=.75 \ Fc=.5 \ Cje=4.973p \ Mje=.4146 \ Vje=.75 \ Tr=4.673n \ Tf=821.7p \ Itf=.35 \ Vtf=4 \ Xtf=7 \ Rb=10)$ 

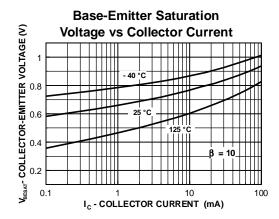
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

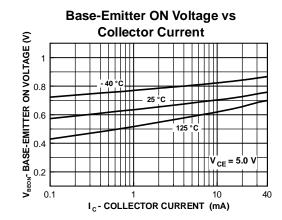
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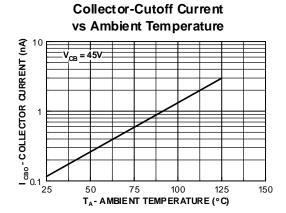
## **Typical Characteristics**







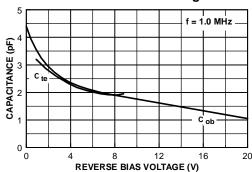




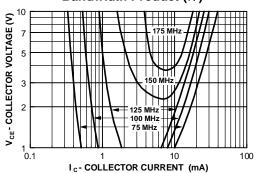
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#### Typical Characteristics (continued)

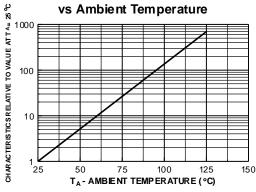
# Input and Output Capacitance vs Reverse Bias Voltage



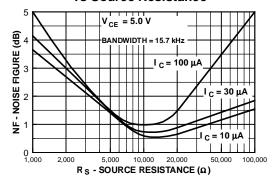
## Contours of Constant Gain Bandwidth Product (f<sub>T</sub>)



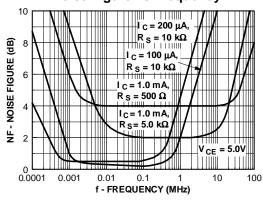
## Normalized Collector-Cutoff Current vs Ambient Temperature



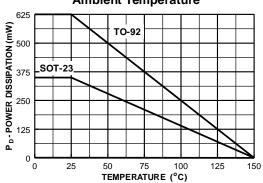
## Wideband Noise Frequency vs Source Resistance



#### **Noise Figure vs Frequency**



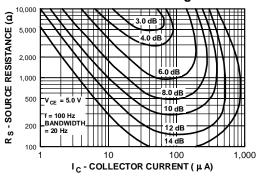
#### Power Dissipation vs Ambient Temperature



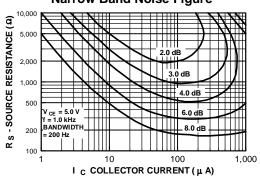
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## Typical Characteristics (continued)

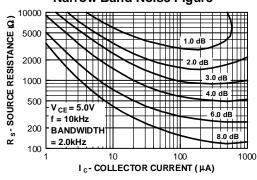
# Contours of Constant Narrow Band Noise Figure



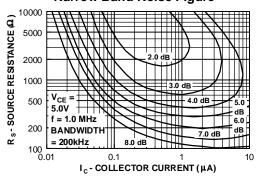
#### Contours of Constant Narrow Band Noise Figure



#### Contours of Constant Narrow Band Noise Figure



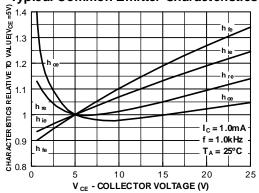
# **Contours of Constant Narrow Band Noise Figure**



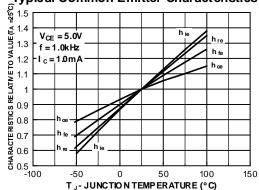
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## **Typical Common Emitter Characteristics** (f = 1.0 kHz)

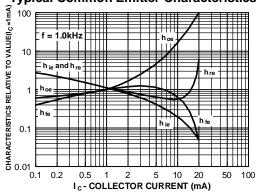
#### **Typical Common Emitter Characteristics**



#### Typical Common Emitter Characteristics



#### **Typical Common Emitter Characteristics**



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